

Specification:

Please make the following changes to the Specification:

In the paragraph of page 1, lines 20-23 (i.e. the last paragraph on the page):

The invention relates to digital imaging with time-to-threshold A/D conversion, particularly to low-cost, low-complexity structures for converting analog sensor outputs to digital indicator signals in CMOS image sensor arrays.
In CMOS image sensor arrays, the sensors are photodetectors.

In the paragraph of page 6, lines 4-6:

The present invention is a time-to-threshold A/D conversion structure for photodetector-based image sensors, with CMOS digital logic or logic-type circuits, such as inverters, for comparing ~~sensor~~ photodetector signal levels to implicit threshold levels.

In the paragraph of page 9, lines 8-13:

Figure 1A depicts a photodiode **10** connected to a ground wire **12** and a reset transistor **14**. Reset transistor **14** is connected to reset reference bus **16**. Photodiode **10** is also connected to the input of an inverter **20**. Inverter **20** has positive power supply bus **18** and ground wire **12** as power rails, and provides a digital indicator signal at digital inverter output **22**. The output of inverter **20** is connected to a count recorder not shown in the figure. In Fig. 1A and the other figures, photodiode **10** is the photodetector, but other photodetector structures and configurations are possible.

In the paragraph heading of page 13, line 23:

DESCRIPTION – A PRIOR ART CMOS ACTIVE PIXEL SENSOR CELL

In the paragraph of page 17, lines 11-16:

Figure 2B shows a embodiment of the present invention in an array defined by array boundary 36. Externally, a counter 38 tracks elapsed time. The digital count signals are provided to the ~~sensors~~ sensor cells in the array via a column line conditioner 40. Each sensor cell is connected to column line conditioner 40 via a bi-directional bus 42. Also external to the array are a power supply 44 and a reference and control signal generator 46.